NSN 5961-01-006-8833 Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-006-8833
Inclosure Material:
Metal
Overall Length:
0.250 inches
Overall Diameter:
0.352 inches
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Terminal
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
6.0 gate voltage, dc
Current Rating Per Characteristic:
15.00 amperes source cutoff current absolute
Power Rating Per Characteristic:
100.0 milliwatts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius junction
Test Data Document:
18876-10669445 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
3 uninsulated wire lead
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
No
Fiig:
A110a0